

FIG. 1

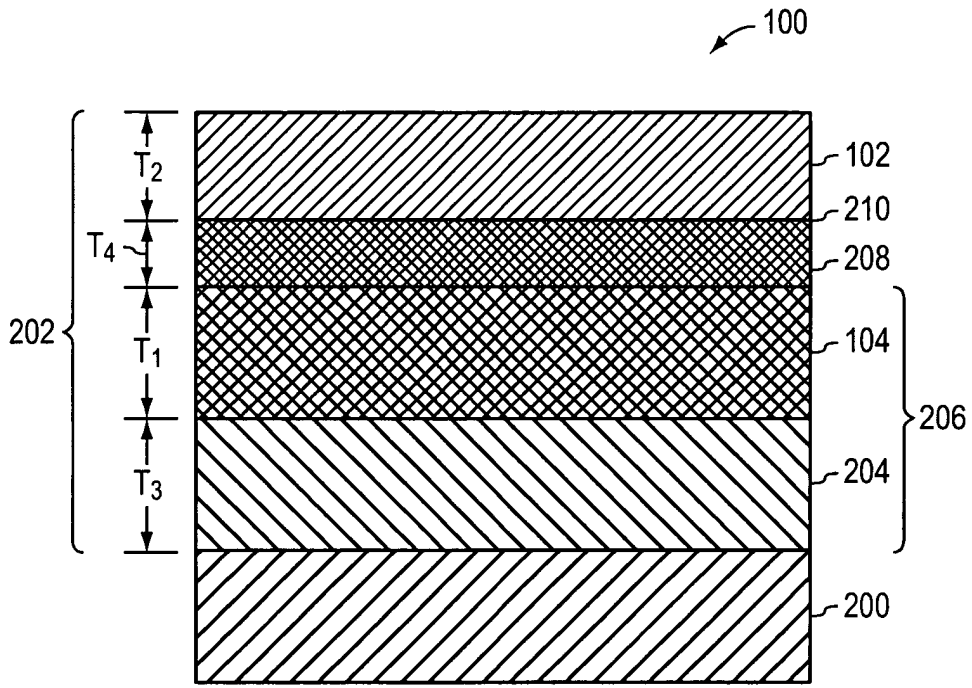
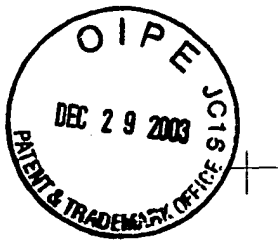
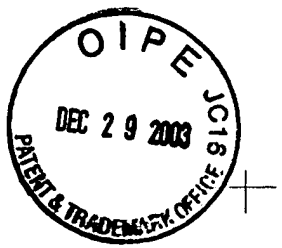


FIG. 2



"Gate Material for Semiconductor Device
Fabrication" by Lochtefeld et al.
Serial No. 10/691,007 Filed 10/22/2003
Natasha C. Us (617) 310-8327
Reg. No. 44,381
Atty Docket No. ASC-060

3/10

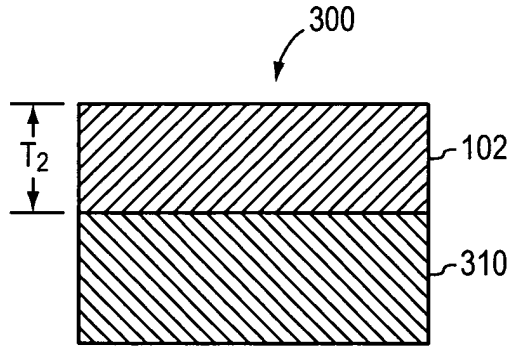


FIG. 3



"Gate Material for Semiconductor Device
Fabrication" by Lochtefeld et al.
Serial No. 10/691,007 Filed 10/22/2003
Natasha C. Us (617) 310-8327
Reg. No. 44,381
Atty Docket No. ASC-060

4/10

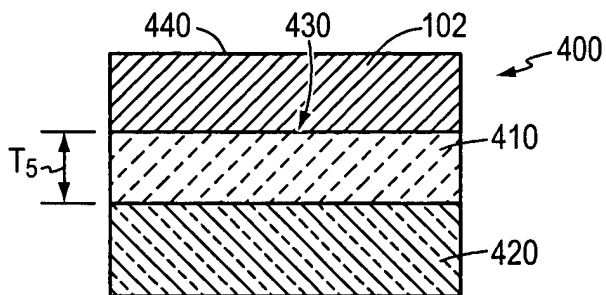


FIG. 4



"Gate Material for Semiconductor Device
Fabrication" by Lochtefeld et al.
Serial No. 10/691,007 Filed 10/22/2003
Natasha C. Us (617) 310-8327
Reg. No. 44,381
Atty Docket No. ASC-060

5/10

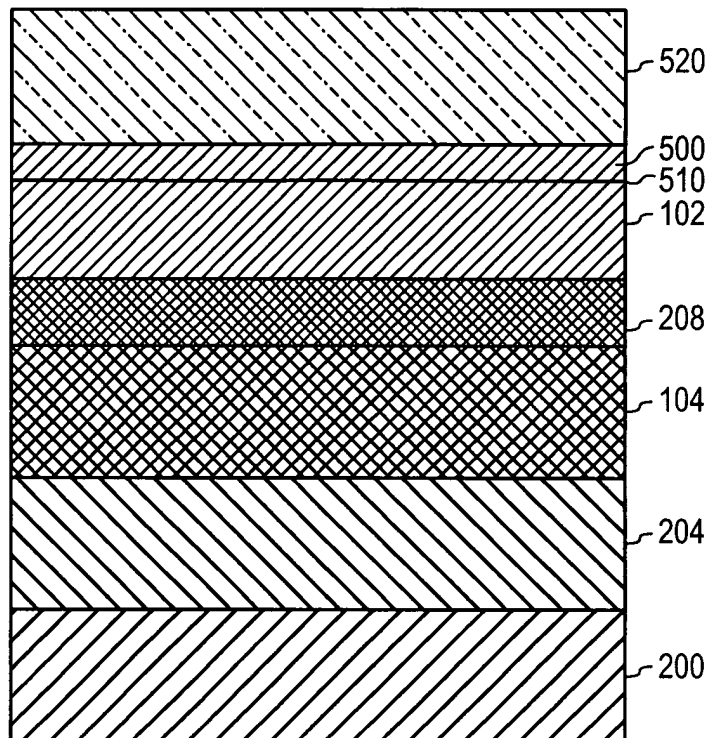


FIG. 5



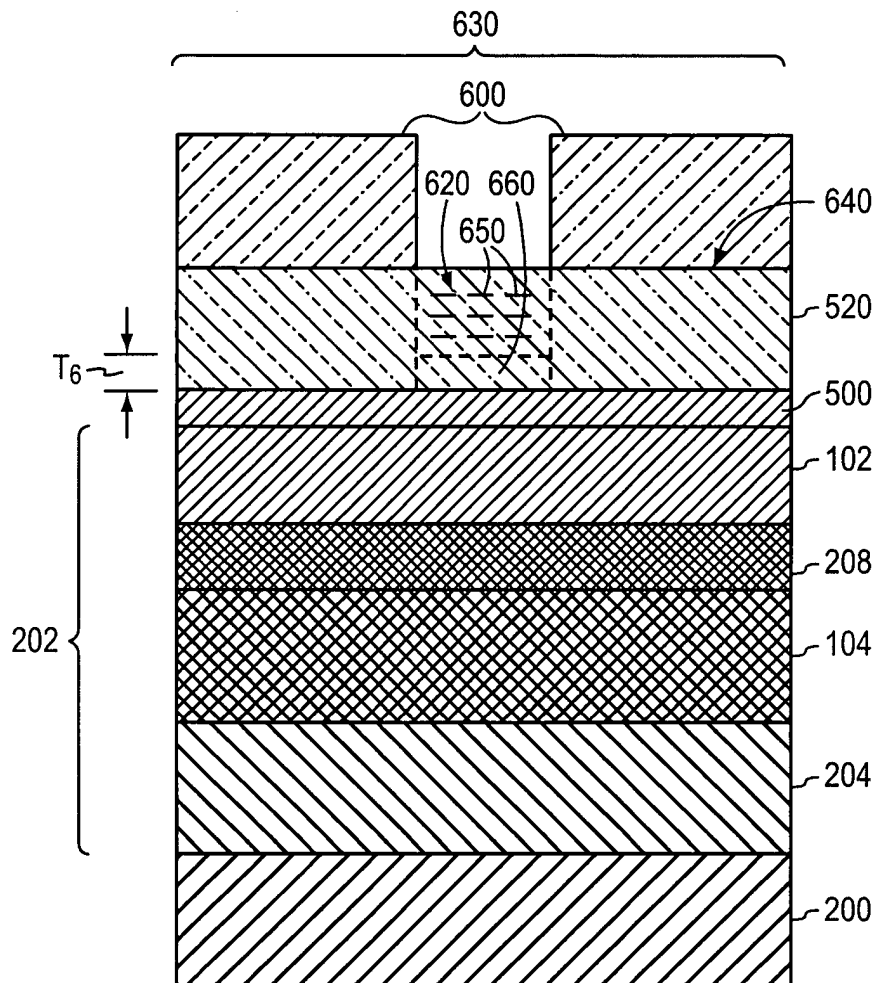


FIG. 6



7/10

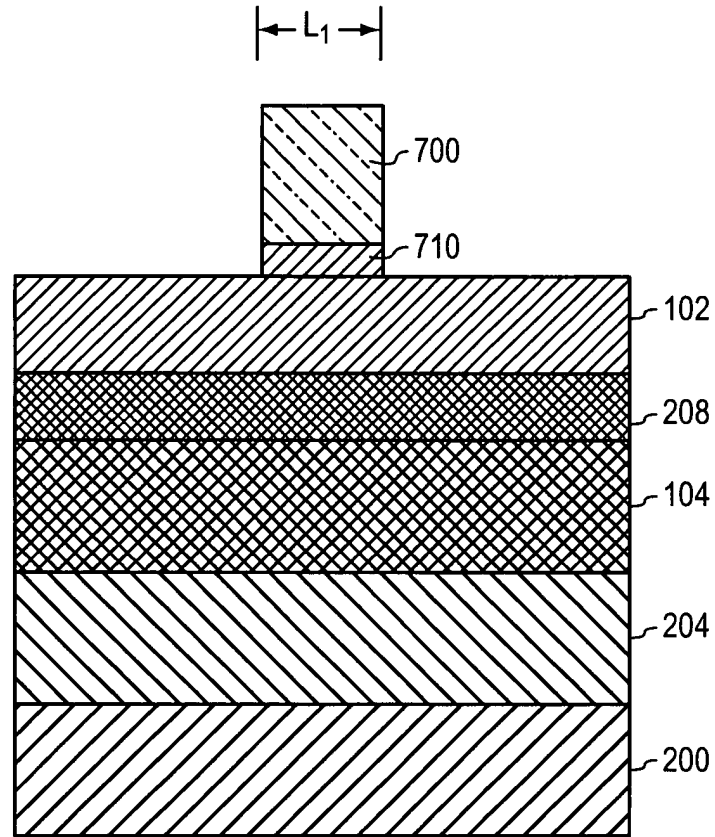


FIG. 7



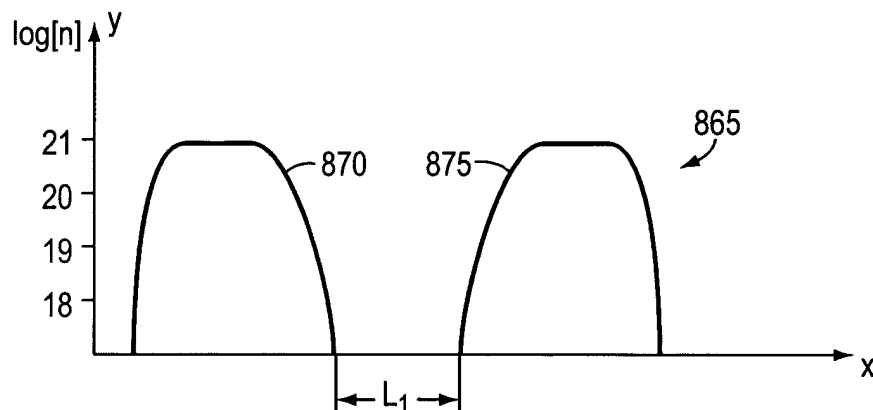


FIG. 8B

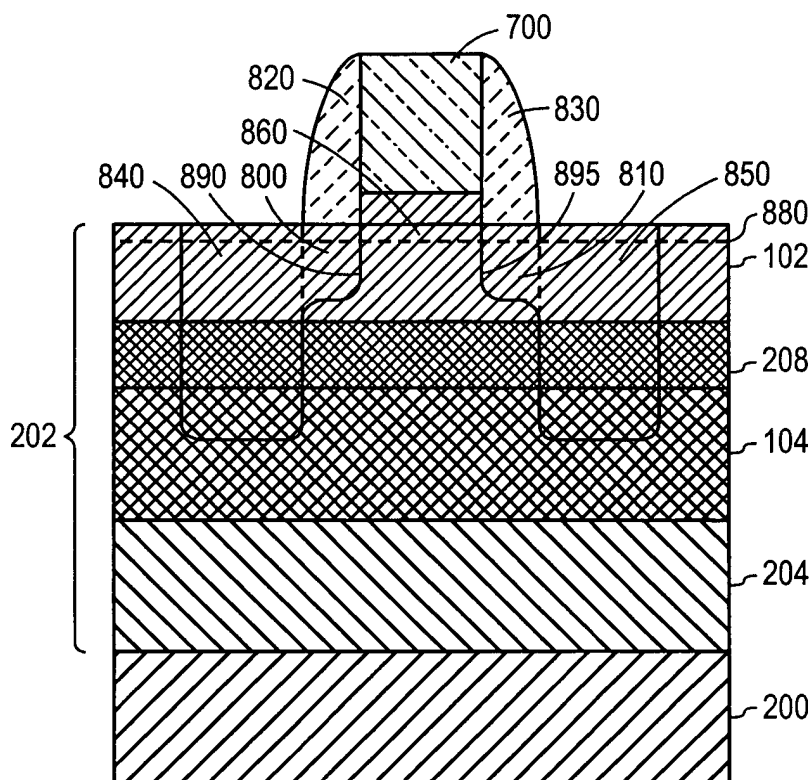


FIG. 8A

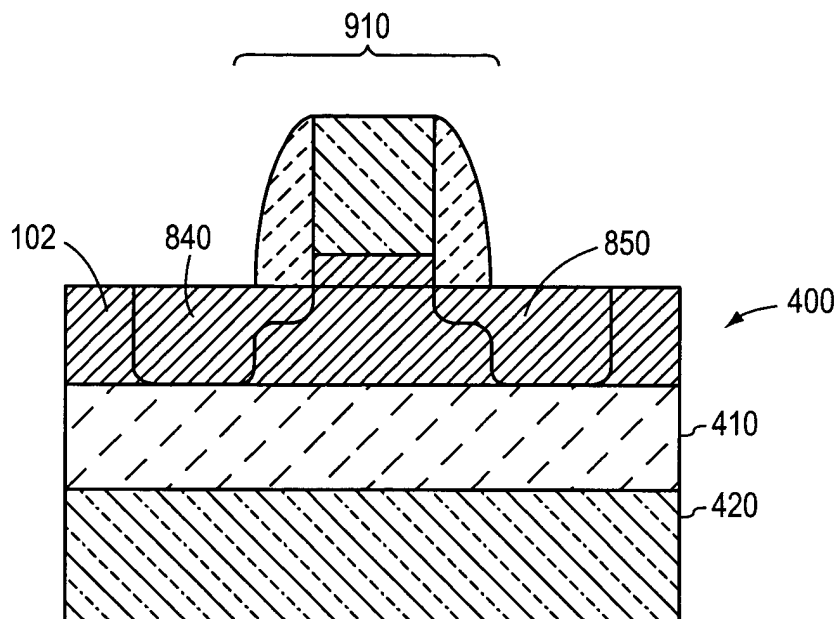


FIG. 10